

N-channel 600 V, 0.200 Ω typ., 16 A MDmesh II Power MOSFET in a PowerFLAT™ 8x8 HV package

Datasheet – production data

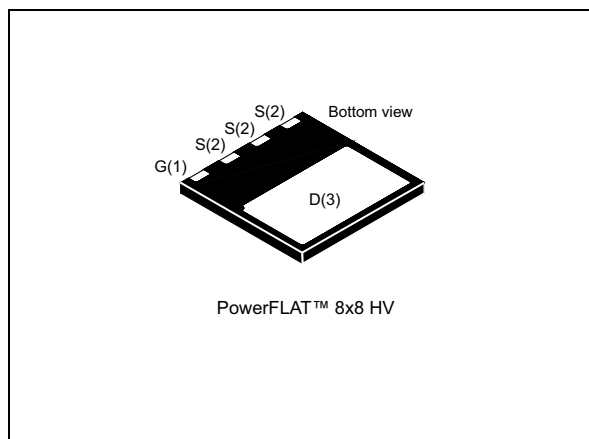
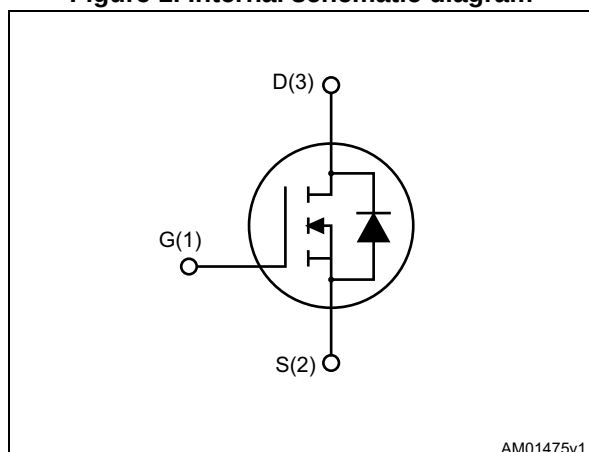


Figure 1. Internal schematic diagram



Features

Order code	$V_{DS} @ T_{Jmax}$	$R_{DS(on)} max$	I_D
STL24NM60N	650 V	0.215 Ω	16 A ⁽¹⁾

1. The value is rated according to $R_{thj-case}$

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order code	Marking	Package	Packaging
STL24NM60N	24NM60N	PowerFLAT™ 8x8 HV	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	16	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	10	A
$I_{DM}^{(1),(3)}$	Drain current (pulsed)	64	A
$I_D^{(2)}$	Drain current (continuous) at $T_{amb} = 25\text{ }^\circ\text{C}$	3.3	A
$I_D^{(2)}$	Drain current (continuous) at $T_{amb} = 100\text{ }^\circ\text{C}$	1.5	A
$I_{DM}^{(2),(3)}$	Drain current (pulsed)	13.2	A
$P_{TOT}^{(2)}$	Total dissipation at $T_{amb} = 25\text{ }^\circ\text{C}$	3	W
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	125	W
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	4	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	300	mJ
$dv/dt^{(4)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	$^\circ\text{C}$

1. The value is rated according to $R_{thj-case}$
2. When mounted on FR-4 board of inch², 2oz Cu
3. Pulse width limited by safe operating area
4. $I_{SD} \leq 16\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS(peak)} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1	$^\circ\text{C}/\text{W}$
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb max	45	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of inch², 2oz Cu.

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 600\text{ V}$			1	μA
		$V_{GS} = 0, V_{DS} = 600\text{ V}, T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 25\text{ V}$			± 100	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$		0.2	0.215	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{GS} = 0, V_{DS} = 50\text{ V}, f = 1\text{ MHz}$	-	1330	-	pF
C_{oss}	Output capacitance		-	80	-	pF
C_{rss}	Reverse transfer capacitance		-	3.2	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0\text{ to }480\text{ V}$	-	182	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	5	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}, I_D = 16\text{ A},$ $V_{GS} = 10\text{ V}$ (see Figure 15)	-	44	-	nC
Q_{gs}	Gate-source charge		-	7	-	nC
Q_{gd}	Gate-drain charge		-	24	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off delay time	$V_{DD} = 300\text{ V}$, $I_D = 8\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14 and 19)	-	11.5	-	ns
t_r	Rise time		-	16.5	-	ns
t_c	Cross time		-	73	-	ns
t_f	Fall time		-	37	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		16	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		64	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 16\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 16\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 16)	-	340		ns
Q_{rr}	Reverse recovery charge		-	4.6		μC
I_{RRM}	Reverse recovery current		-	27		A
t_{rr}	Reverse recovery time	$I_{SD} = 16\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16)	-	404		ns
Q_{rr}	Reverse recovery charge		-	5.7		μC
I_{RRM}	Reverse recovery current		-	28		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration= 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

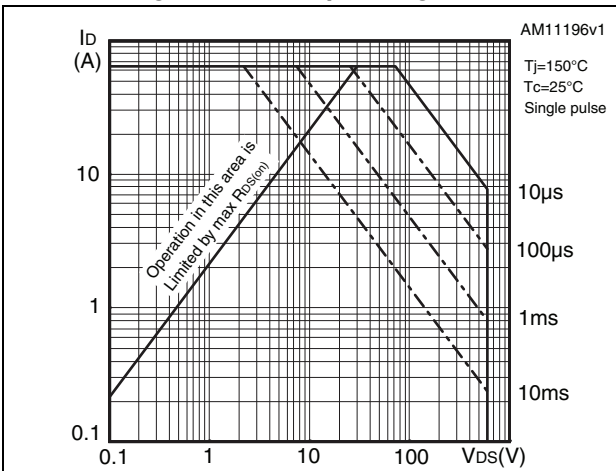


Figure 3. Thermal impedance

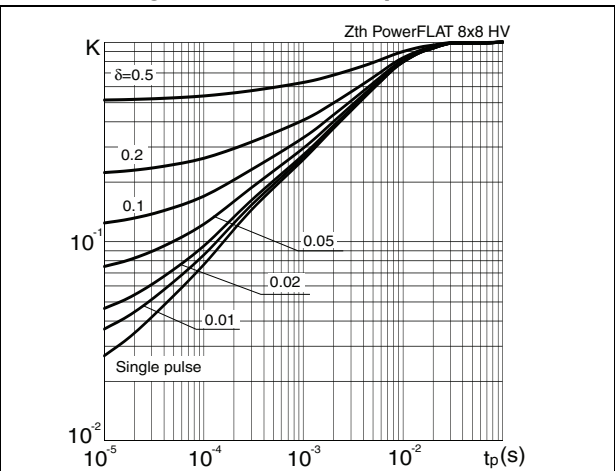


Figure 4. Output characteristics

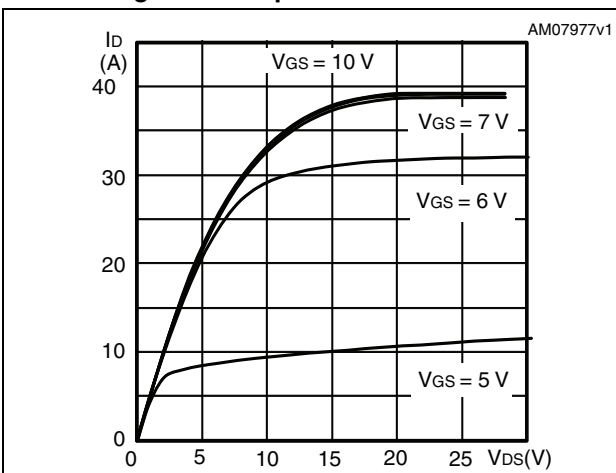


Figure 5. Transfer characteristics

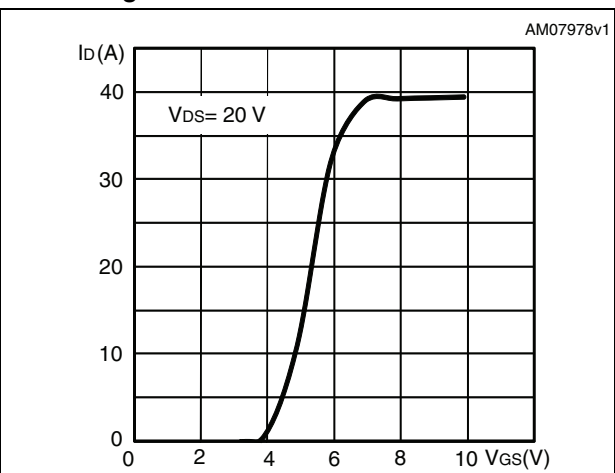


Figure 6. Gate charge vs gate-source voltage

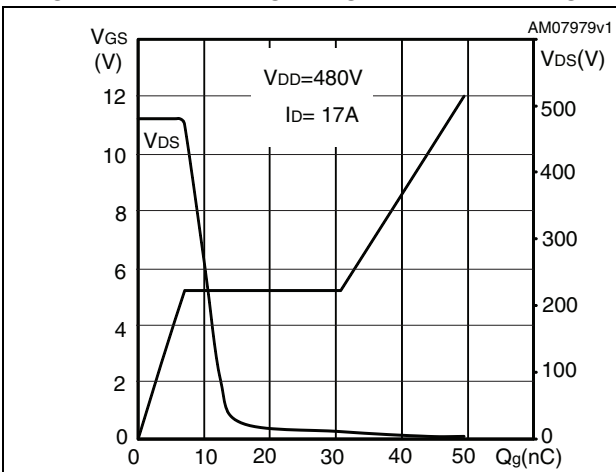


Figure 7. Static drain-source on-resistance

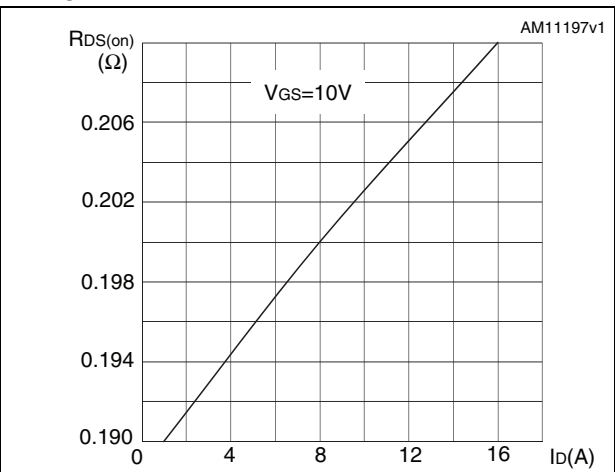


Figure 8. Capacitance variations

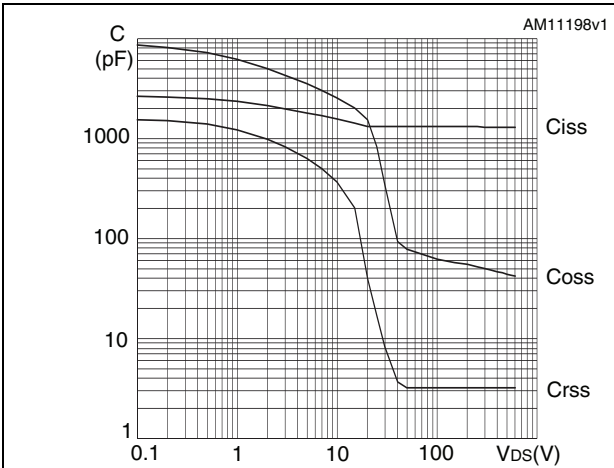


Figure 9. Output capacitance stored energy

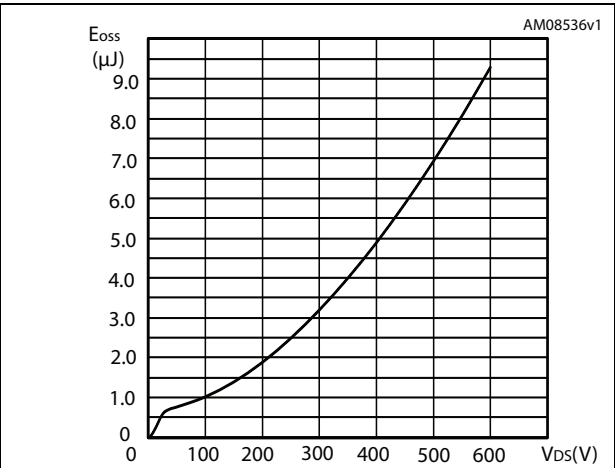


Figure 10. Normalized gate threshold voltage vs temperature

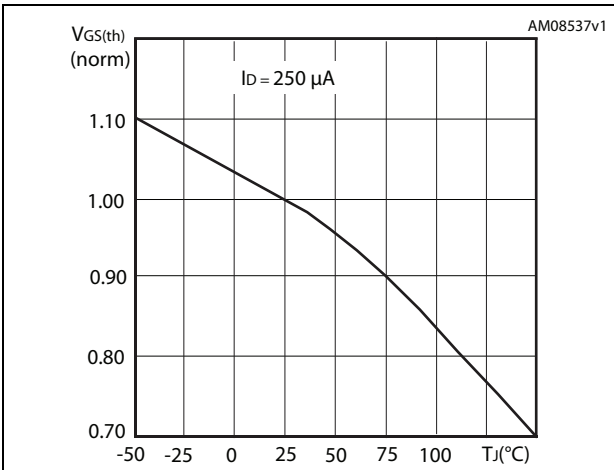


Figure 11. Normalized on-resistance vs temperature

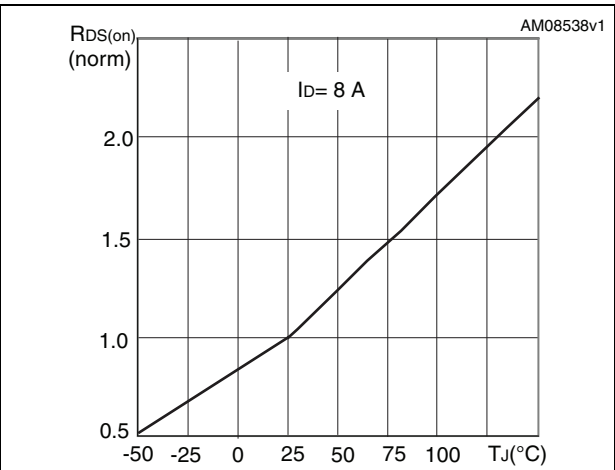


Figure 12. Normalized $V_{(BR)DSS}$ vs temperature

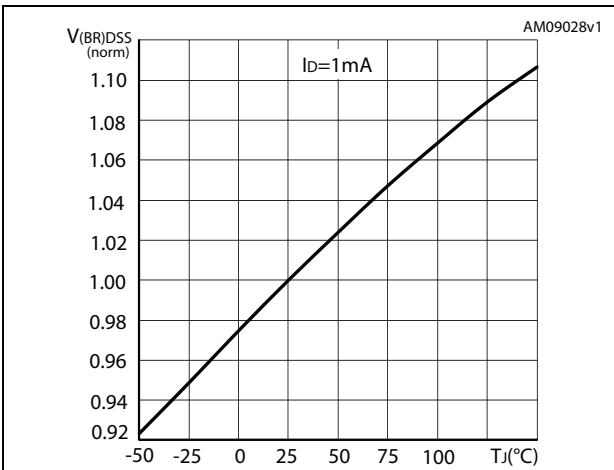
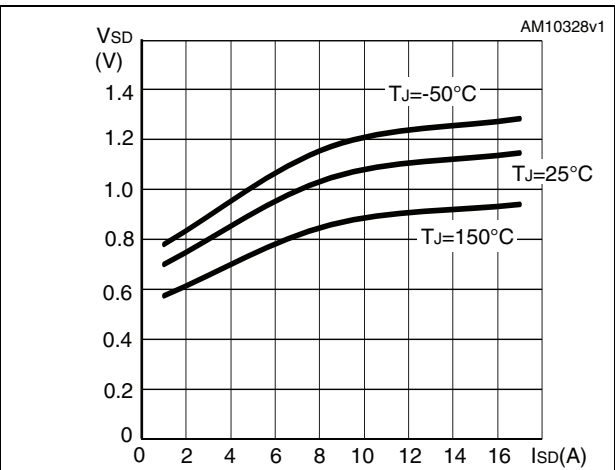


Figure 13. Source-drain diode forward characteristics



3 Test circuits

Figure 14. Switching times test circuit for resistive load

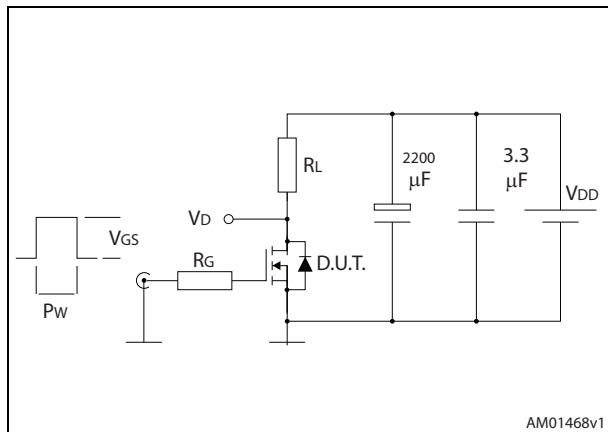


Figure 15. Gate charge test circuit

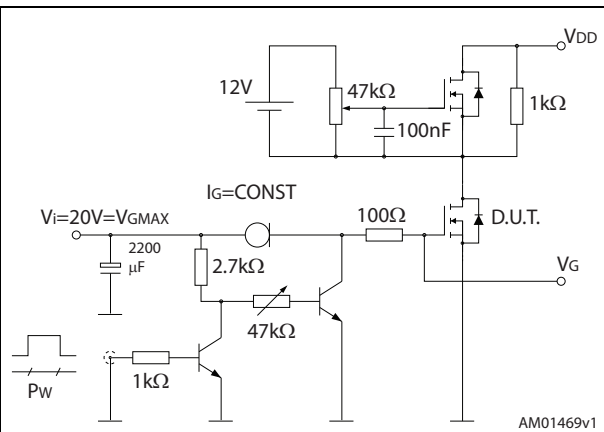


Figure 16. Test circuit for inductive load switching and diode recovery times

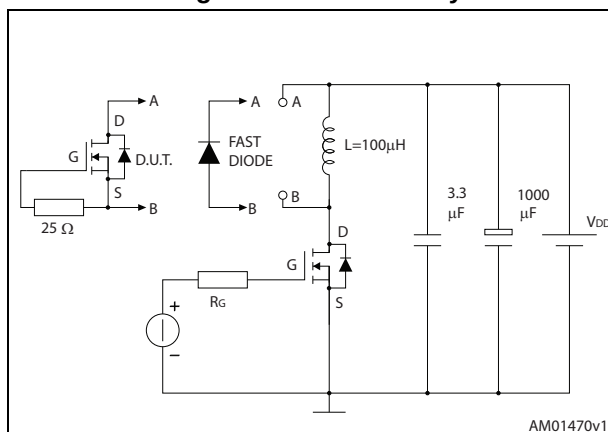


Figure 17. Unclamped inductive load test circuit

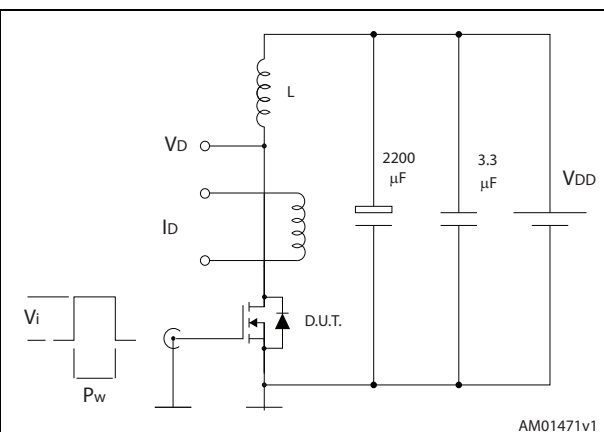


Figure 18. Unclamped inductive waveform

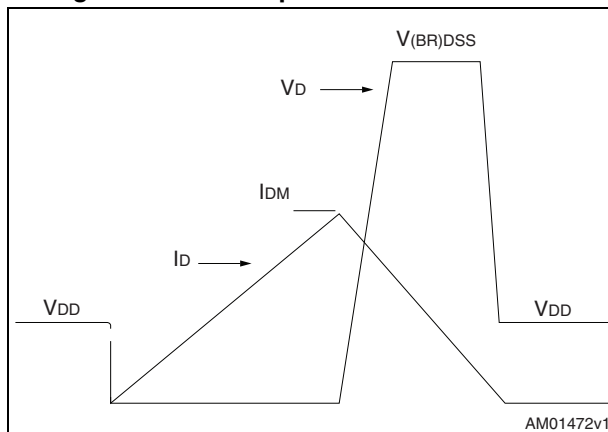
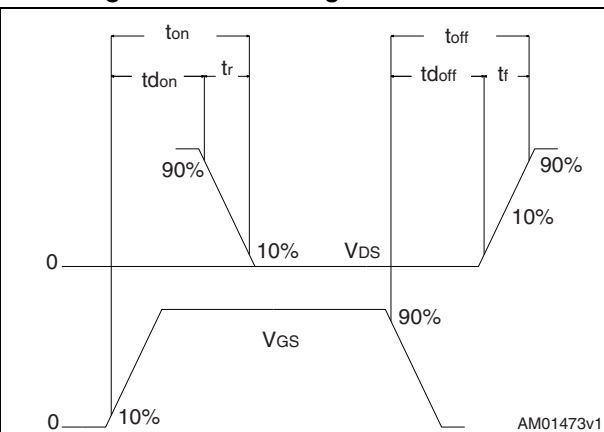


Figure 19. Switching time waveform



4 Package mechanical data

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Figure 20. PowerFLAT™ 8x8 HV drawing mechanical data

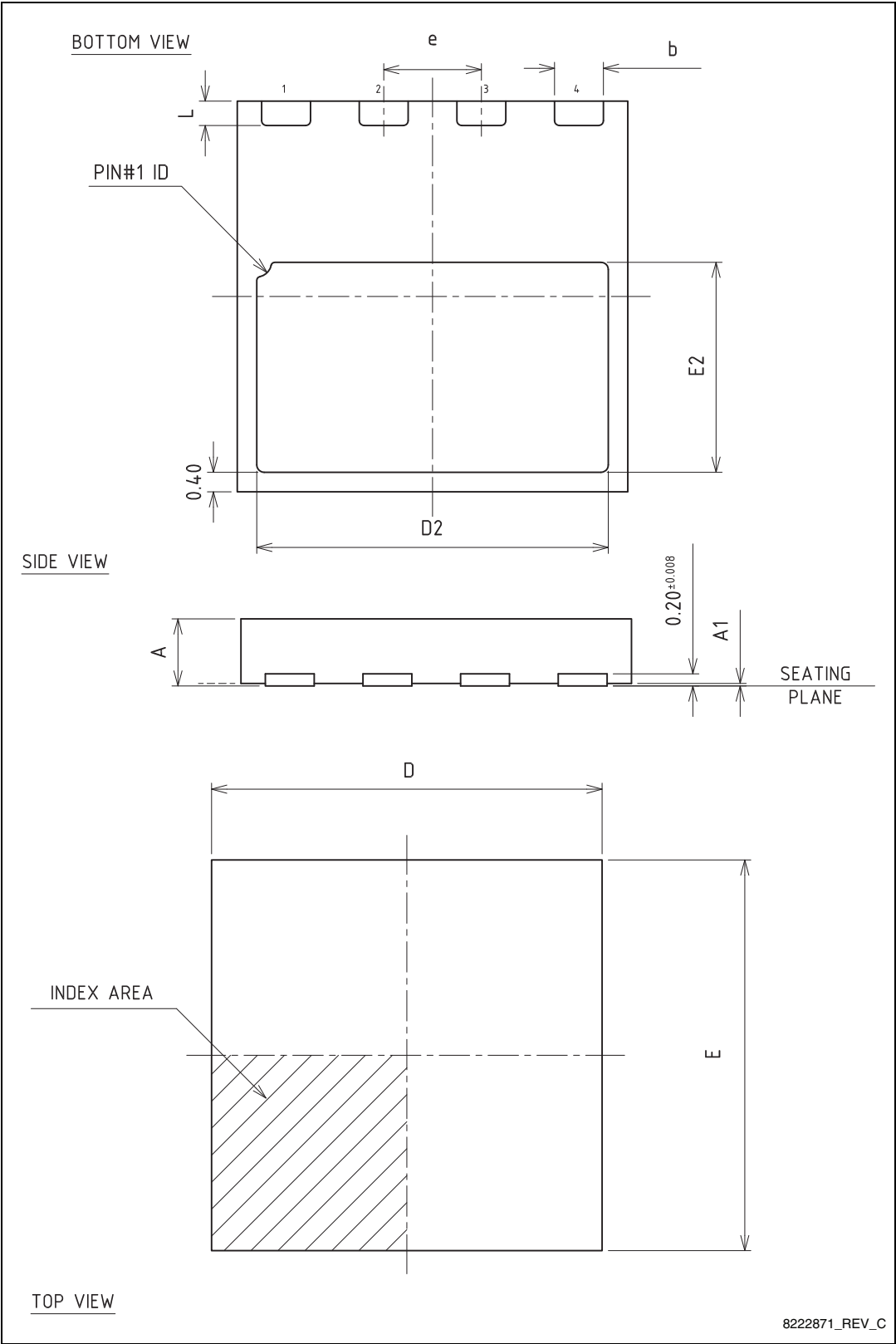
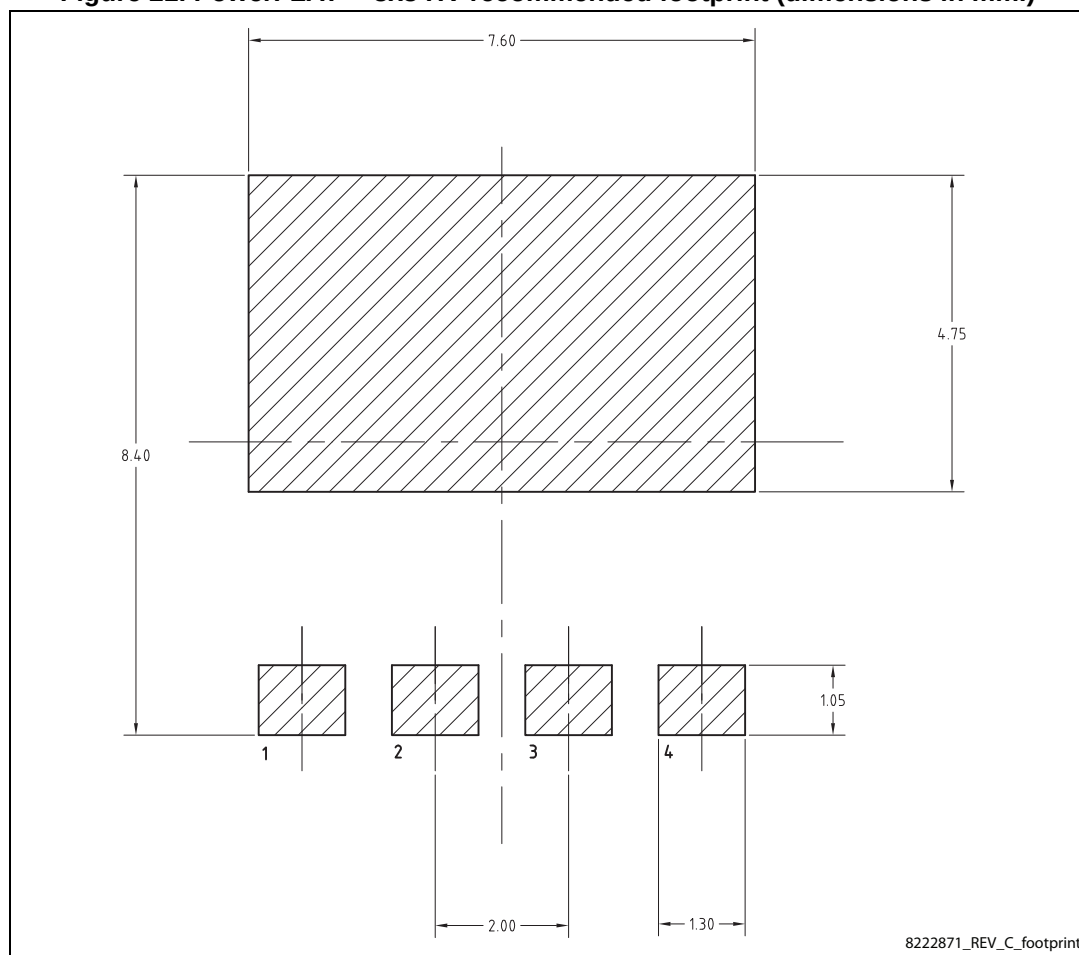


Table 8. PowerFLAT™ 8x8 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
b	0.95	1.00	1.05
D		8.00	
E		8.00	
D2	7.05	7.20	7.30
E2	4.15	4.30	4.40
e		2.00	
L	0.40	0.50	0.60

Figure 21. PowerFLAT™ 8x8 HV recommended footprint (dimensions in mm.)



5 Packaging mechanical data

Figure 22. PowerFLAT™ 8x8 HV tape

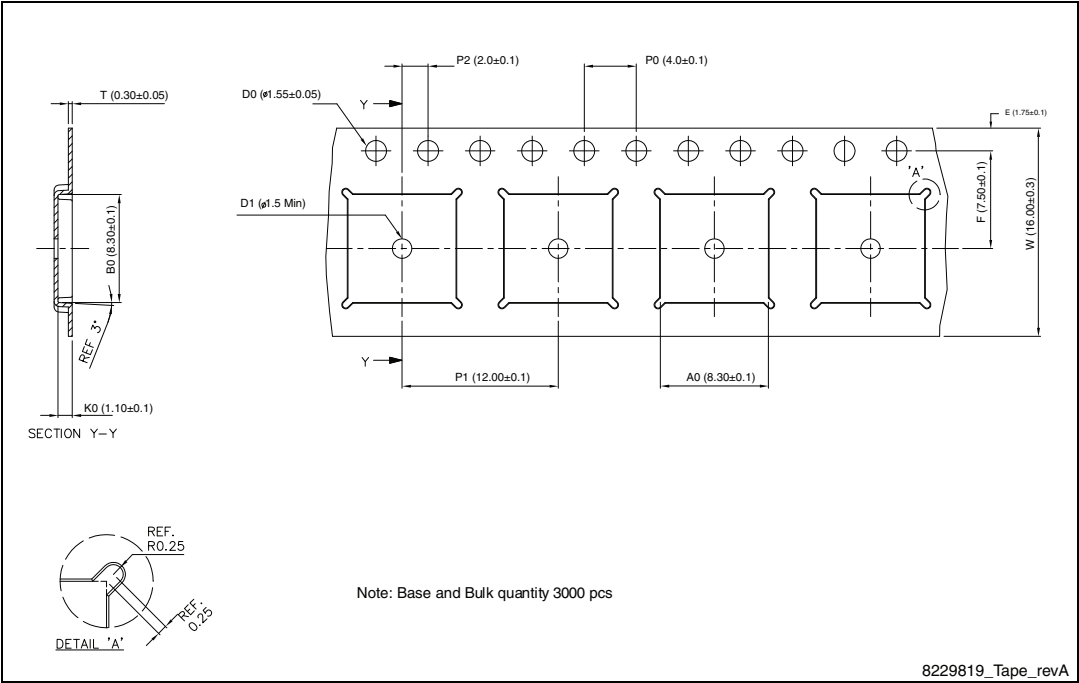


Figure 23. PowerFLAT™ 8x8 HV package orientation in carrier tape.

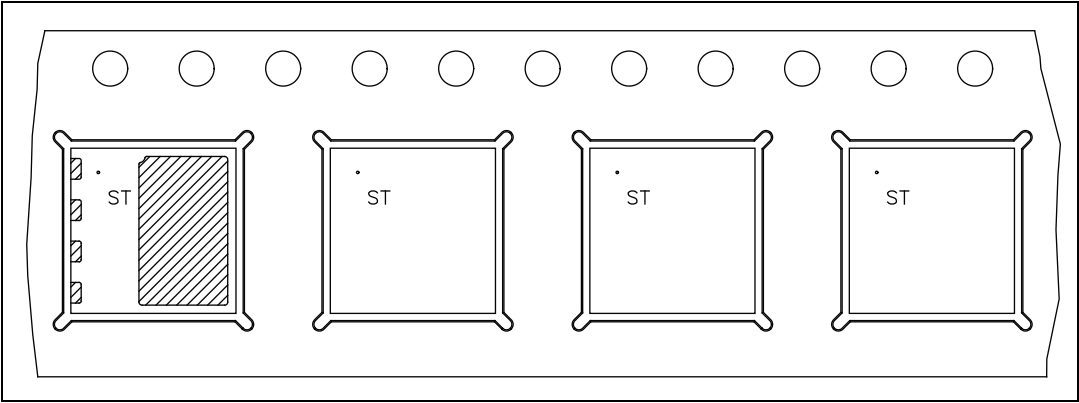
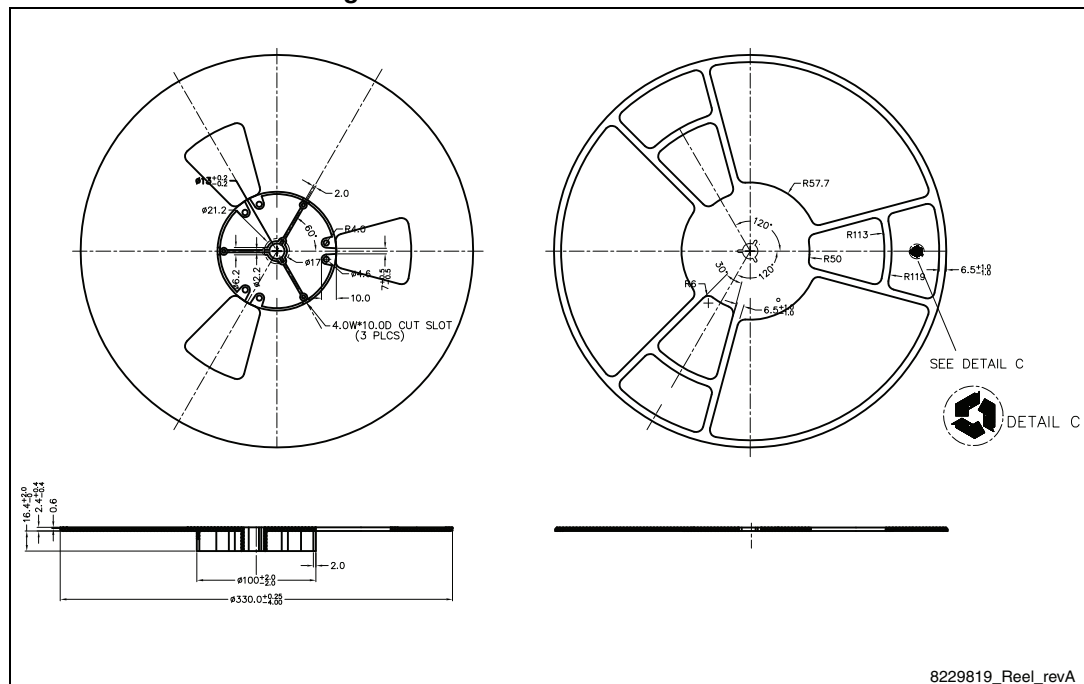


Figure 24. PowerFLAT™ 8x8 HV reel



6 Revision history

Table 9. Document revision history

Date	Revision	Changes
05-Jan-2011	1	First release.
10-Nov-2011	2	– Section 4: Package mechanical data has been updated – Minor text changes
04-Jun-2013	3	– Section 2.1: Electrical characteristics (curves) has been added – Document status promoted from preliminary data to production data – Minor text changes – Added: I_{DM} parameter on Table 2
24-Jul-2014	4	– Modified: the entire typical values in Table 6 – Updated: Section 4: Package mechanical data – Minor text changes

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